

2N3416 2N3417



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	50	V	
V _{CBO}	Collector-Base Voltage	50	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	500	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		2N3416 / 2N3417		
P _D	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

NPN General Purpose Amplifier (continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions Min		Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	50		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	50		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	V _{CB} = 25 V, I _E = 0 V _{CB} = 18 V, I _E = 0, T _A = 100°C		100 15	nA μA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		100	nA

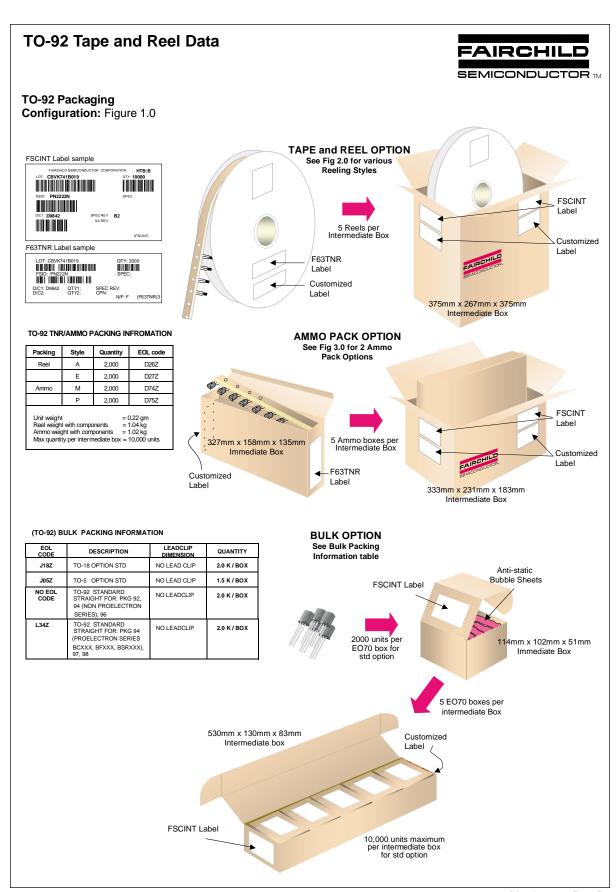
ON CHARACTERISTICS*

h _{FE}	DC Current Gain	$V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$			
		2N3416	75	225	
		2N3417	180	540	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$		0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$	0.6	1.3	V

SMALL SIGNAL CHARACTERISTICS

h _{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$			
		f = 1.0 kHz	2N3416	75	
			2N3417	180	

^{*}Pulse Test: Pulse Width $\leq\!300~\mu\text{s},$ Duty Cycle $\leq\!2.0\%$

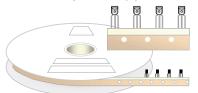


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



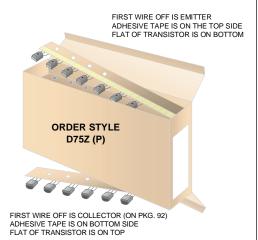
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

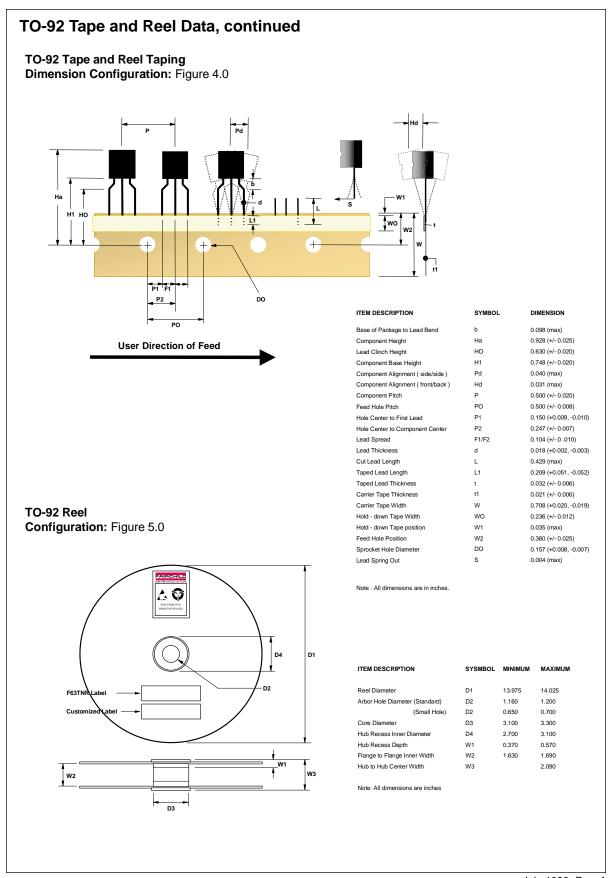
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B



TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

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